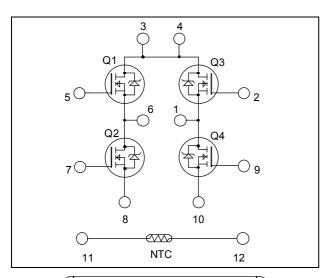
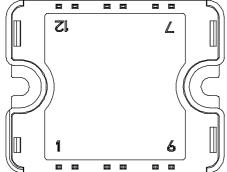


Full - Bridge MOSFET Power Module

$$\begin{split} V_{DSS} &= 500V \\ R_{DSon} &= 130 m\Omega \text{ typ } \text{ } \text{ } \text{ } \text{Tj} = 25^{\circ}\text{C} \\ I_D &= 25\text{A} \text{ } \text{ } \text{ } \text{C} = 25^{\circ}\text{C} \end{split}$$





Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 8TM FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		500	V
Ţ	Continuous Dusin Comment	$T_c = 25^{\circ}C$	25	
I_{D}	Continuous Drain Current	$T_c = 80$ °C	19	A
I_{DM}	Pulsed Drain current			
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		156	mΩ
P_D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	208	W
I_{AR}	Avalanche current (repetitive and non repetitive)		21	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
T	Zero Gate Voltage Drain Current	$V_{\rm DS} = 500 \rm V$	$T_j = 25^{\circ}C$			250	^
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V$	$T_j = 125$ °C			1000	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 21A$			130	156	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 1 \text{mA}$		3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}$				±100	nA

Dynamic Characteristics

•	ic Characteristics					
Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		5448		
C_{oss}	Output Capacitance	$V_{\rm DS} = 25V$		735		pF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		72		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		170		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		38		nC
Q_{gd}	Gate – Drain Charge	$I_D = 21A$		80		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C		29		
$T_{\rm r}$	Rise Time	$\begin{aligned} V_{GS} &= 15V \\ V_{Bus} &= 333V \\ I_D &= 21A \end{aligned}$		35		
$T_{d(off)}$	Turn-off Delay Time			80		ns
T_{f}	Fall Time	$R_G = 4.7\Omega$		26		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$			25	A
	(Body diode)		$Tc = 80^{\circ}C$			19	А
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -21A$	L			1	V
dv/dt	Peak Diode Recovery					30	V/ns
t _{rr}	Reverse Recovery Time	x 214	$T_j = 25^{\circ}C$			215	ns
		$I_{S} = -21A$ $V_{R} = 100V$	$T_j = 125$ °C			370	113
Q _{rr}	Reverse Recovery Charge	$di_{S}/dt = 100 \text{ A}/\mu\text{s}$	$T_j = 25$ °C		0.90		μC
			$T_j = 125$ °C		2.6		μ

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

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Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance					0.6	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

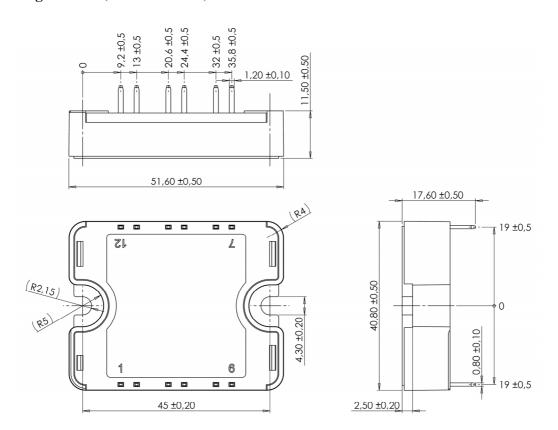
$Temperature \ sensor \ NTC \ (\text{see application note APT0406 on www.microsemi.com for more information}). \\$

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

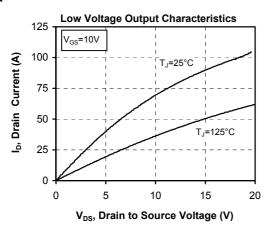
SP1 Package outline (dimensions in mm)

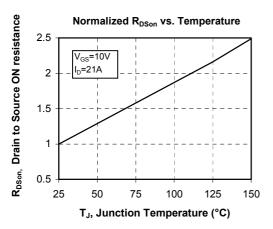


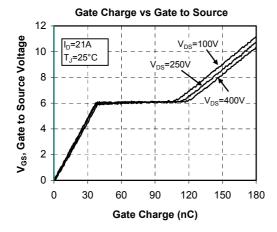
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

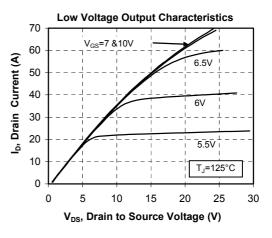


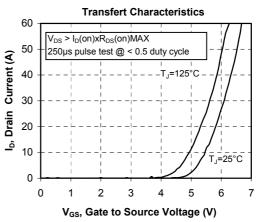
Typical Performance Curve

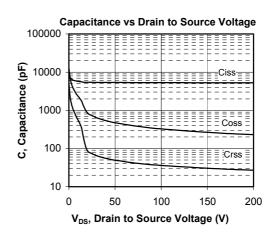






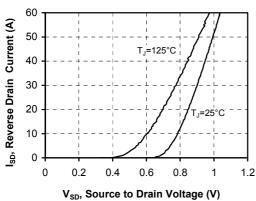


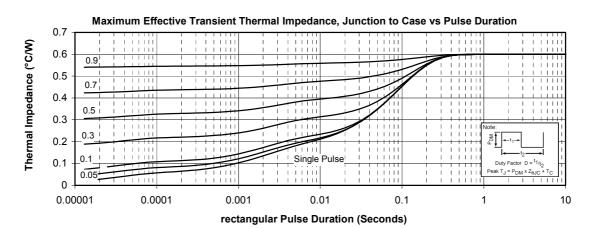






Drain Current vs Source to Drain Voltage





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